

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3221 is N-channel DMOS FET device that features a low gate charge and excellent switching characteristics, and designed for high voltage applications such as switching power supply, AC adapter.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3211	Isolated TO-220

FEATURES

- Low gate charge
 $Q_G = 9 \text{ nC TYP. (} V_{DD} = 450 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 2.0 \text{ A)}$
- Gate voltage rating $\pm 30 \text{ V}$
- Low on-state resistance
 $R_{DS(on)} = 4.4 \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 1.0 \text{ A)}$
- Avalanche capability ratings
- Isolated TO-220 package

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	600	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 30	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 2.0	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 8.0	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	2.0	W
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T2}	25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	2.0	A
Single Avalanche Energy ^{Note2}	E_{AS}	2.7	mJ
Diode Recovery dv/dt ^{Note3}	dv/dt	3.5	V/ns

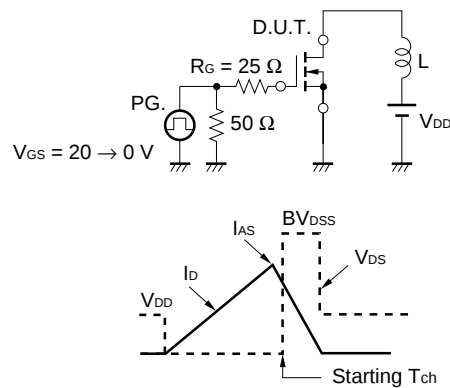
- Notes**
1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
 2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 150 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$
 3. $I_F \leq 1.0 \text{ A}$, $V_{clamp} = 600 \text{ V}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $T_A = 25^\circ\text{C}$

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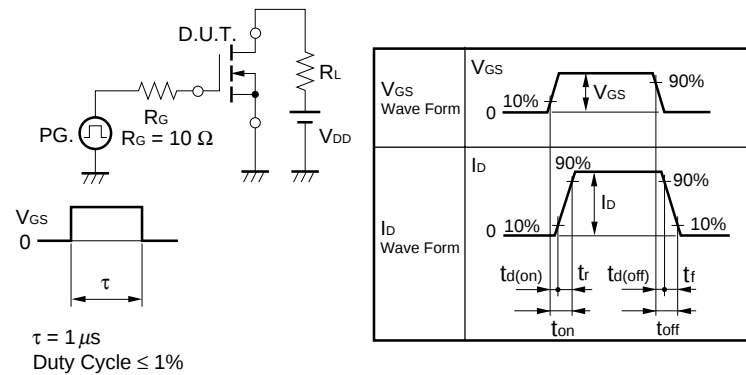
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V			100	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5		3.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 1.0 A	0.5			S
Drain to Source On-state Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 1.0 A		3.3	4.4	Ω
Input Capacitance	C _{iss}	V _{DS} = 10 V		290		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		60		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		5		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 150 V, I _D = 1.0 A		7		ns
Rise Time	t _r	V _{GS} = 10 V		2		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		20		ns
Fall Time	t _f			10		ns
Total Gate Charge	Q _G	V _{DD} = 450 V		9		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		2.4		nC
Gate to Drain Charge	Q _{GD}	I _D = 2.0 A		2		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 2.0 A, V _{GS} = 0 V		0.9		V
Reverse Recovery Time	t _{rr}	I _F = 2.0 A, V _{GS} = 0 V		0.9		μs
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		2.0		μC

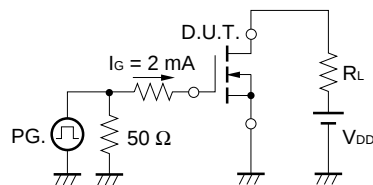
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

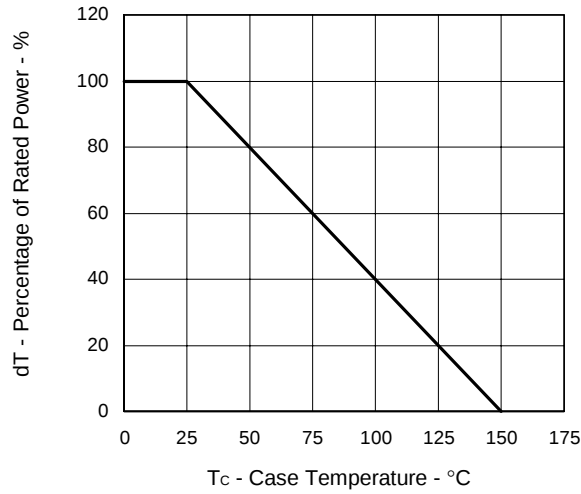


TEST CIRCUIT 3 GATE CHARGE

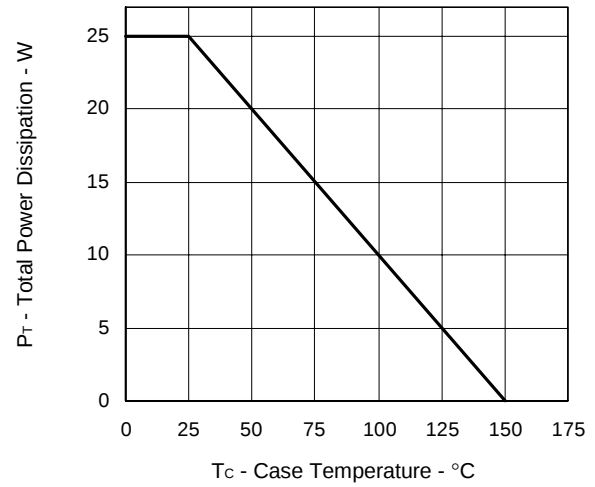


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

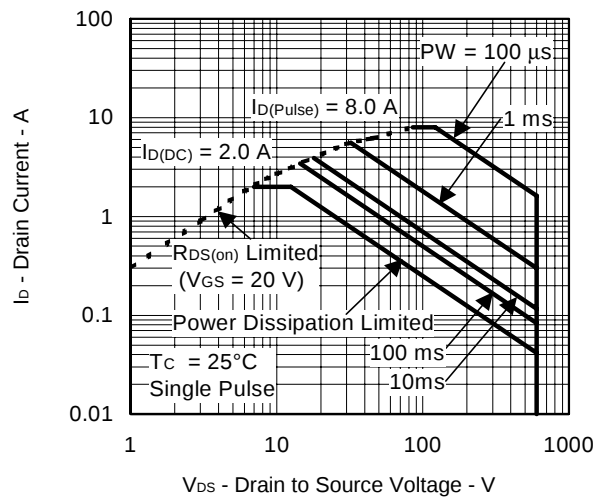
DERATING FACTOR OF FORWARD BIAS
SAFE OPERATING AREA



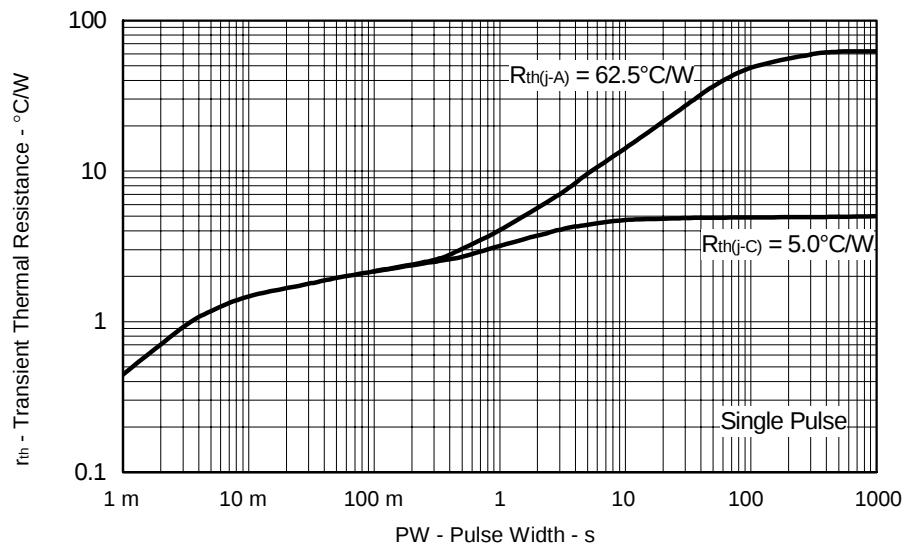
TOTAL POWER DISSIPATION vs.
CASE TEMPERATURE



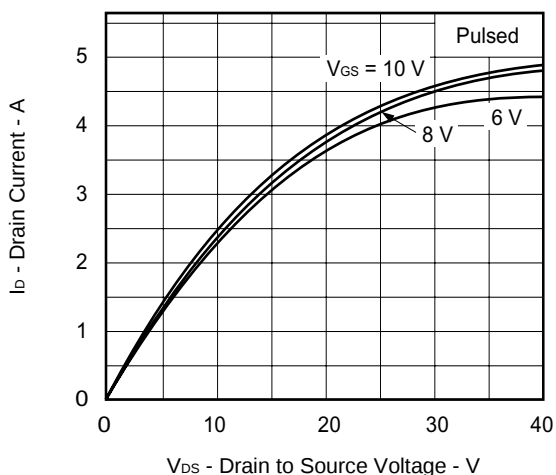
FORWARD BIAS SAFE OPERATING AREA



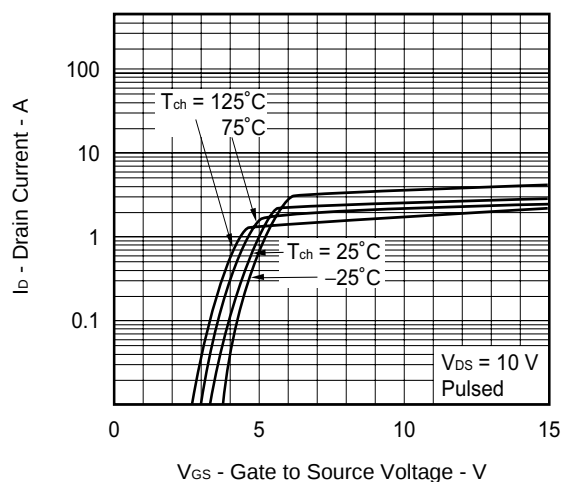
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



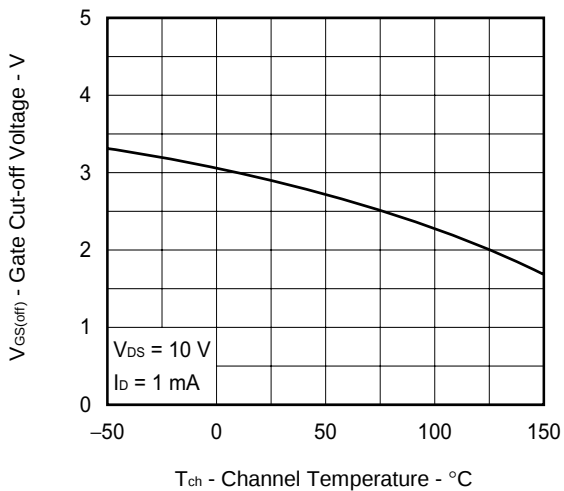
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



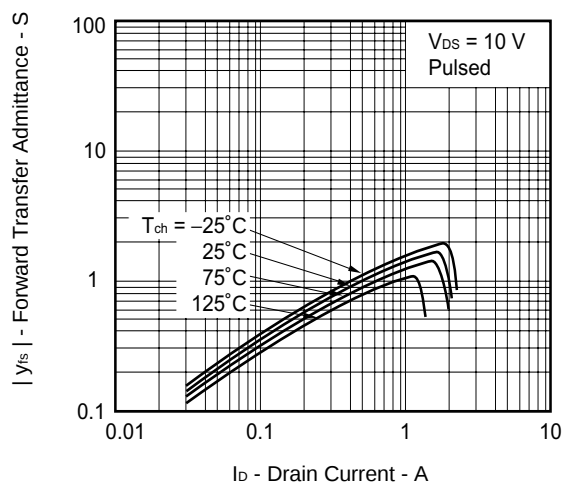
FORWARD TRANSFER CHARACTERISTICS



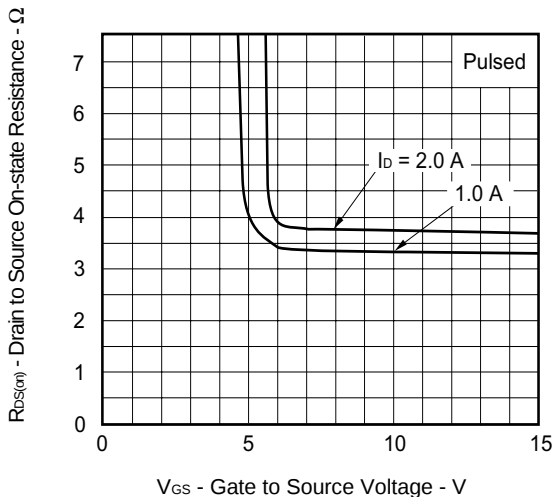
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



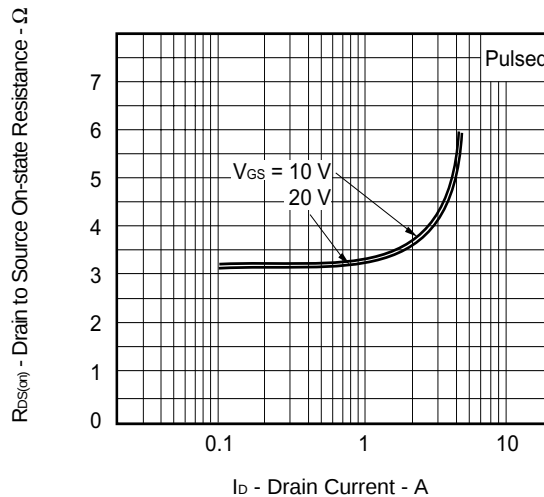
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



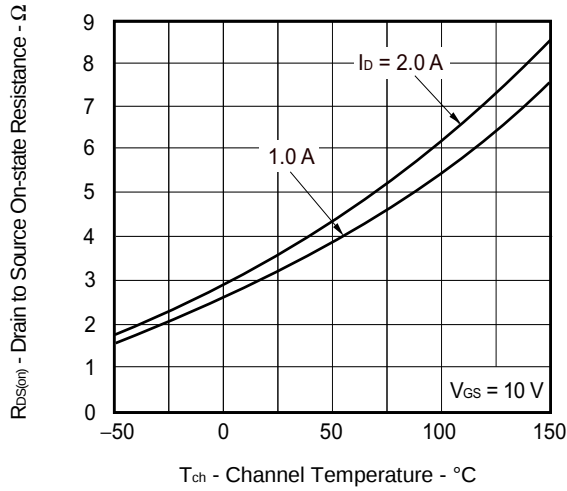
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



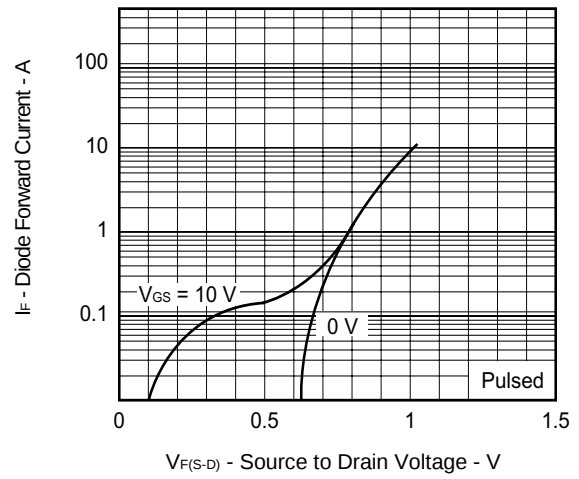
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



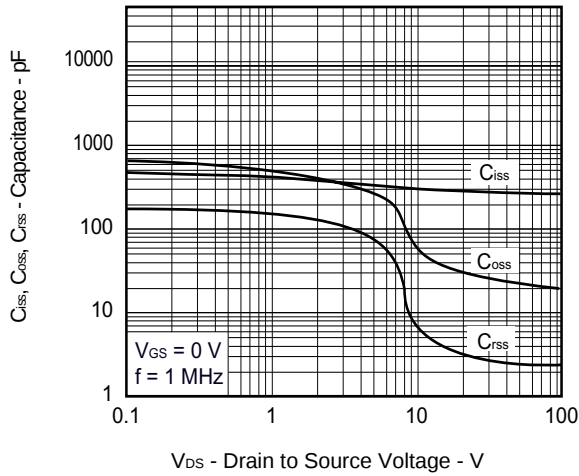
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



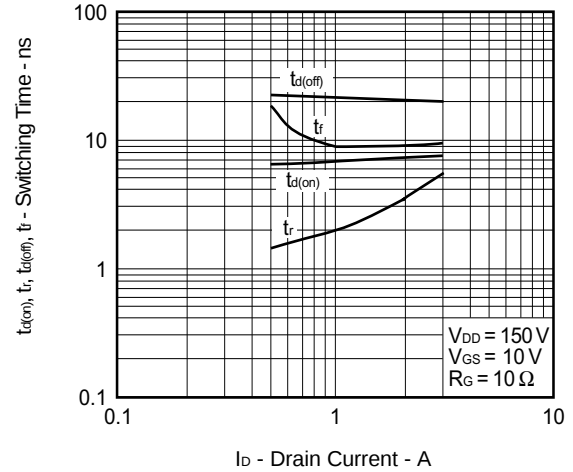
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



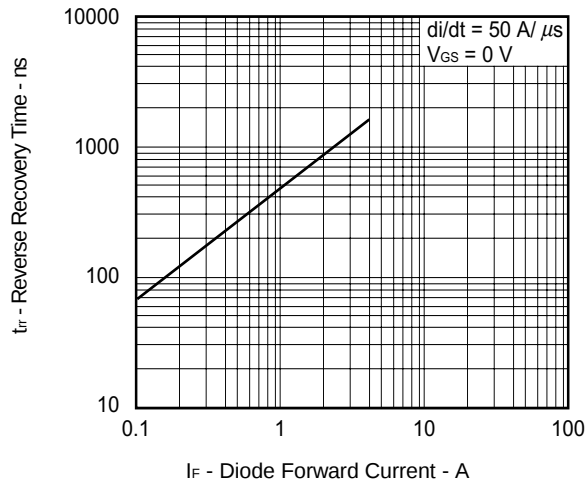
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



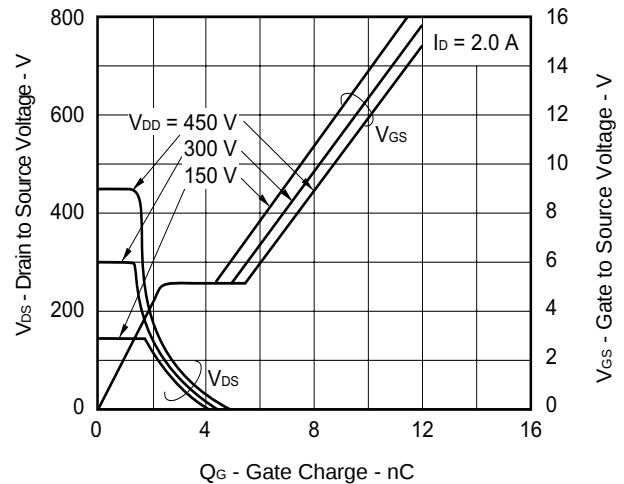
SWITCHING CHARACTERISTICS



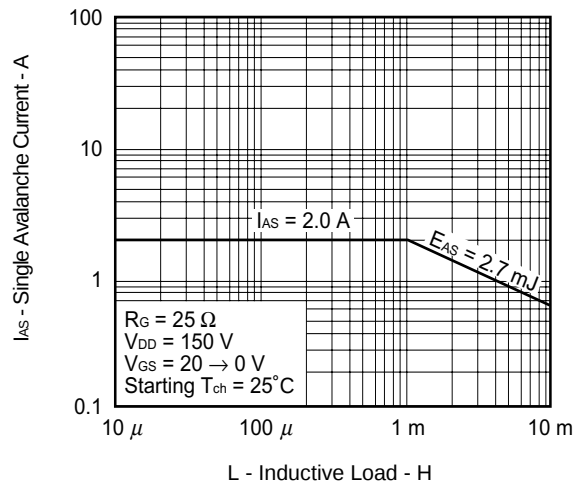
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



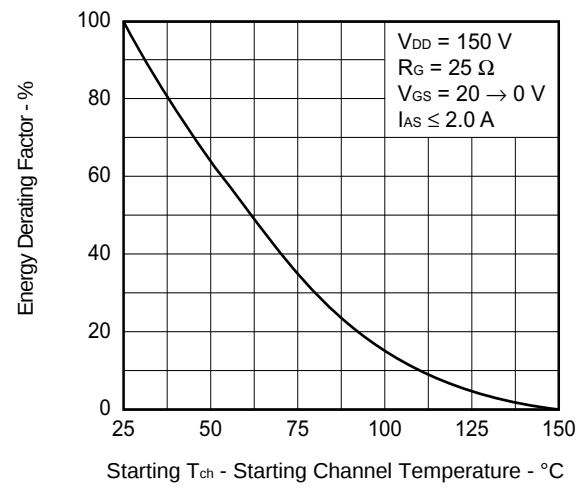
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



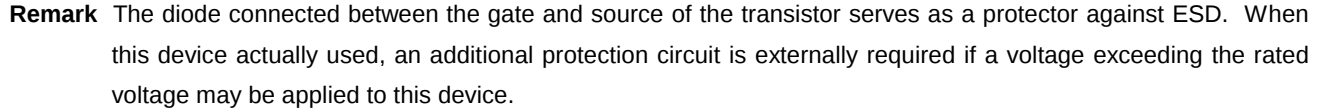
SINGLE AVALANCHE CURRENT vs.
INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY
DERATING FACTOR



Isolated TO-220 (MP-45F)



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